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Preparation and characterization of Cu-Ga-Se thin films synthesized by electrodeposition: effect of complexing agent and supporting electrolyte

A.M. Fernandez^{1,*}, J.A. Turner², B. Lara-Lara¹, and T. G. Deutsch²

¹Instituto de Energías Renovables, Universidad Nacional Autónoma de México, Av. Xochicalco

s/n, Col Rubén Jaramillo, Temixco, Mor., 62580, México.

²National Renewable Energy Laboratory, Golden, Colorado, 80401, USA

Abstract

CuGaSe₂ (CGS) is a semiconductor that has potential use as a photo electrode for solar water splitting. Its wide band

gap and high absorption coefficient make it an ideal candidate for the top absorber in tandem structures. CGS can be

synthesized by several techniques, being electrodeposition the most advantageous from a technical standpoint. Many

reports show that electrodeposition of these films for producing the desired precursor atomic composition can be

aided by using a complexing agent. However, the use of supporting electrolyte and the type of the electrolyte to

improve the atomic composition in the films has never been reported. Using cyclic voltammetry, with complexing

agents and deposition potentials between -0.5 to -0.9 V vs. Ag/AgCl reference electrode atomic ratios close to the

ideal values ([Cu]/[Ga] = 1 and [Se]/[Cu+Ga] = 1), based on atomic composition and morphology analysis are

reported in this work. From the X-ray diffraction (XRD), the as-deposited films exhibit poor crystallinity; however,

the XRD patterns evidence the formation CuGaSe₂ after annealing of the samples.

Key words: Thin films, Electrodeposition, Chalcogenides, Copper-Galium-Selenide.

*Corresponding author

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